

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

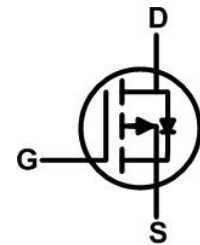
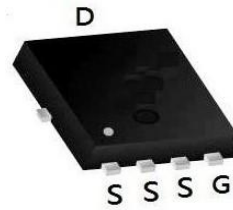

Product Summary

BVDSS	R _{DS(on)}	ID
-20V	4.5mΩ	65A

Description

The XXW65P02D is the high cell density trenched P-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The XXW65P02D meet the RoHS and Green Product requirement with full function reliability approved.

PDFN3333-8L Pin Configuration

Absolute (T_J= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DSS}	Drain-to-Source Voltage	-20	V
I _D	Continuous Drain Current T _C = 25 °C (Silicon limited)	-65	A
	Continuous Drain Current T _C = 25 °C (Package limited) ^{a1}	-40	A
	Continuous Drain Current T _C = 100 °C (Package limited) ^{a1}	-40	A
I _{DM} ^{a1}	Pulsed Drain Current T _C = 25 °C	-200	A
V _{GS}	Gate-to-Source Voltage	±10	V
E _{AS} ^{a2}	Avalanche Energy	98	mJ
P _D	Power Dissipation T _C = 25 °C	41.6	W
	Derating Factor above 25°C	0.33	W/°C
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C

Symbol	Parameter	Max.	Units
R _{θJC}	Junction-to-Case	3.0	°C/W
R _{θJA}	Junction-to-Ambient	64	°C/W

P-Ch 20V Fast Switching MOSFETs
Electrical Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-20V, V_{GS}=0V, T_j=25^\circ\text{C}$	--	--	-1	μA
		$V_{DS}=-16V, V_{GS}=0V, T_j=125^\circ\text{C}$	--	--	-100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=10V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-10V$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=-4.5V, I_D=-19A$	--	4.5	5.6	$m\Omega$
		$V_{GS}=-2.5V, I_D=-19A$	--	5.9	7.6	$m\Omega$
		$V_{GS}=-1.8V, I_D=-19A$	--	8.3	11	$m\Omega$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.7	-1.0	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	--	6.3	--	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = -10V, f = 1.0\text{MHz}$	--	6199	--	μF
C_{oss}	Output Capacitance		--	885.6	--	
C_{riss}	Reverse Transfer Capacitance		--	976	--	

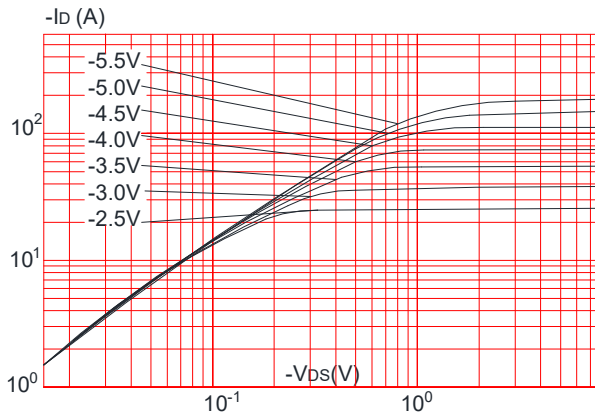
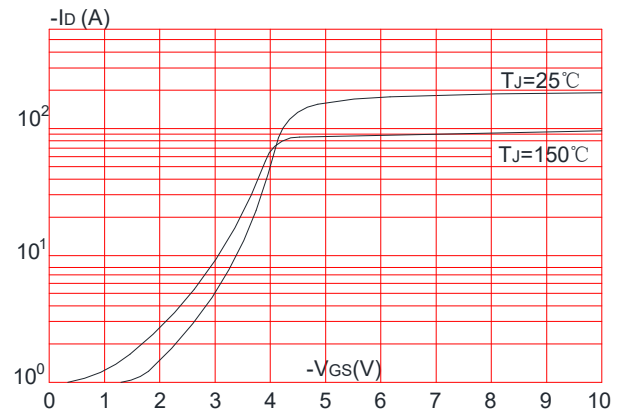
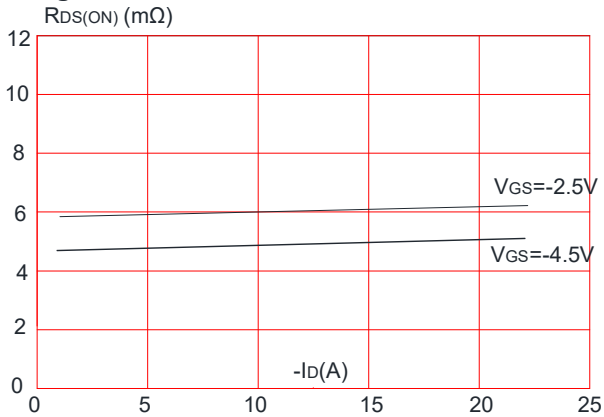
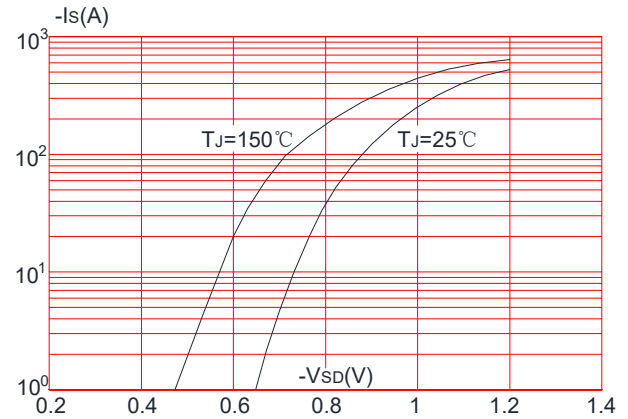
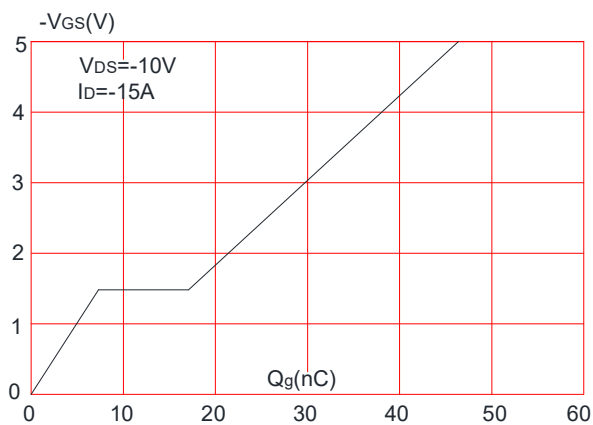
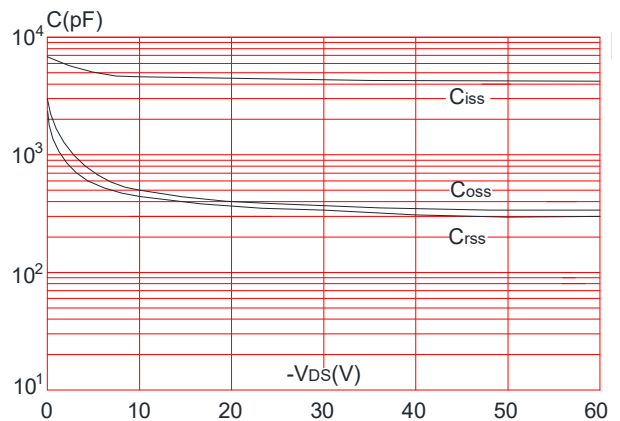
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)	$T_C = 25^\circ\text{C}$	--	--	-65	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	-200	A
V_{SD}	Diode Forward Voltage	$I_S=-19A, V_{GS}=0V$	--	--	-1.2	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

^{a1}: Calculated continuous current based on maximum allowable junction temperature. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.

^{a2}: $L=0.5\text{mH}, I_{AS}=19.8\text{A}$ Start $T_j=25^\circ\text{C}$

^{a3}: Recommend soldering temperature defined by IPC/JEDEC J-STD 020

Typical Performance Characteristics

Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


P-Ch 20V Fast Switching MOSFETs

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

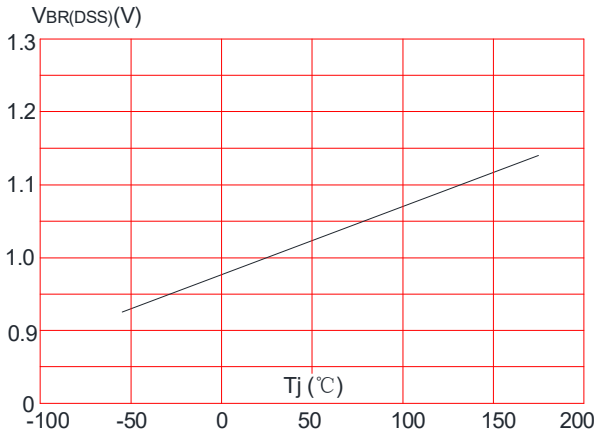


Figure 8: Normalized on Resistance vs. Junction Temperature

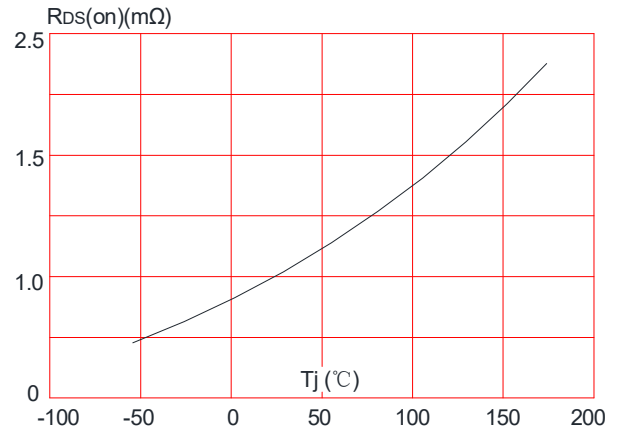


Figure 9: Maximum Safe Operating Area

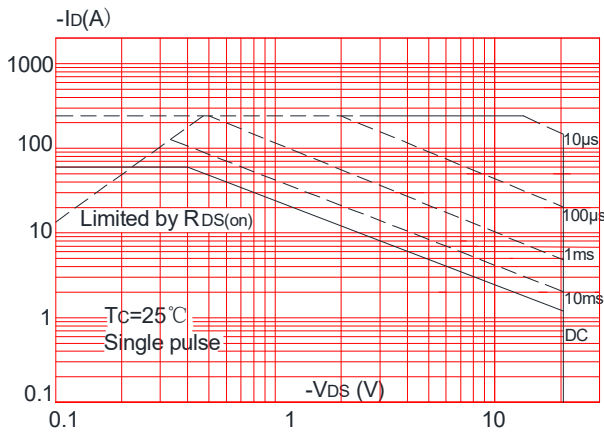


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

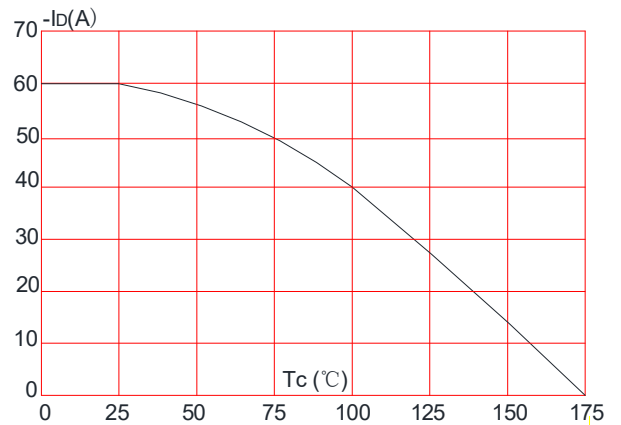
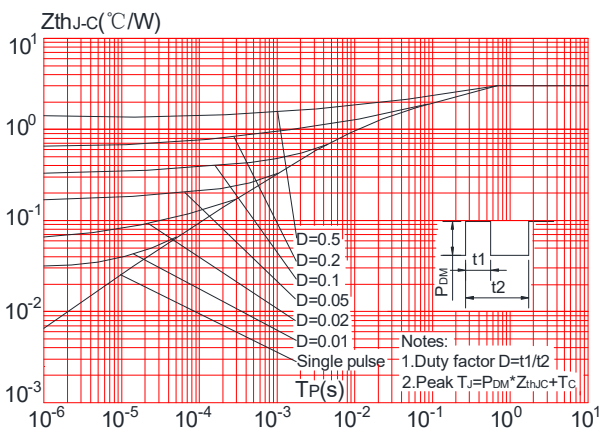


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit and Waveform

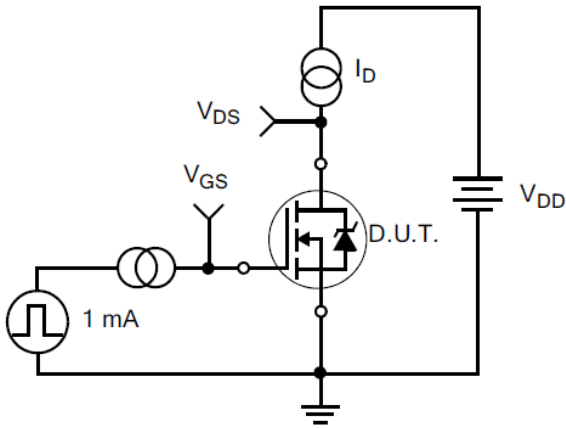


Figure 17. Gate Charge Test Circuit

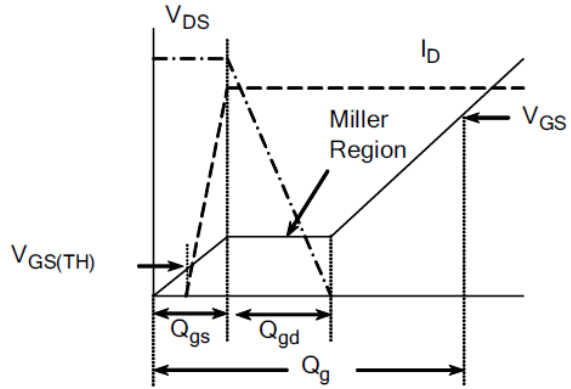


Figure 18. Gate Charge Waveform

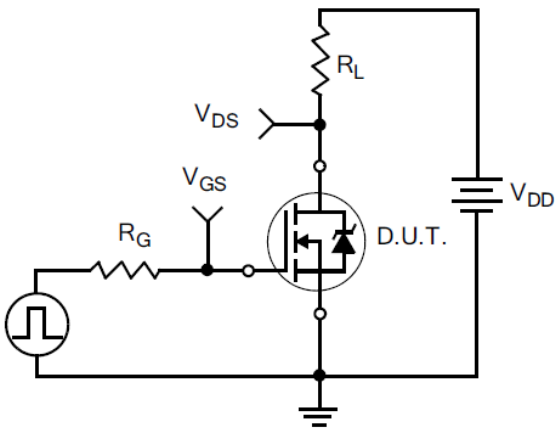


Figure 19. Resistive Switching Test Circuit

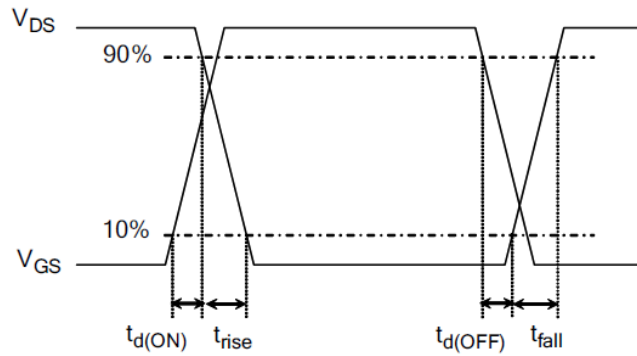


Figure 20. Resistive Switching Waveforms

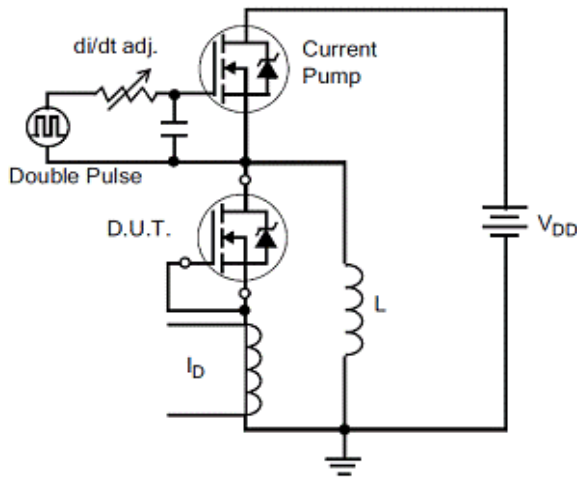


Figure 21. Diode Reverse Recovery Test Circuit

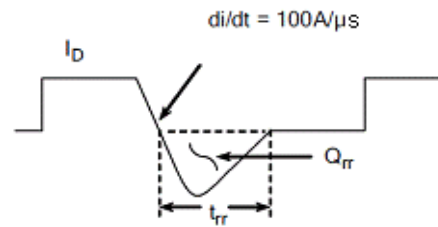


Figure 22. Diode Reverse Recovery Waveform

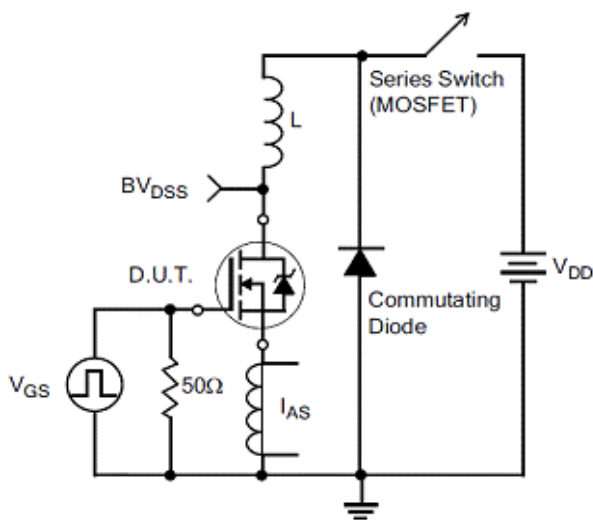


Figure 23. Unclamped Inductive Switching Test Circuit

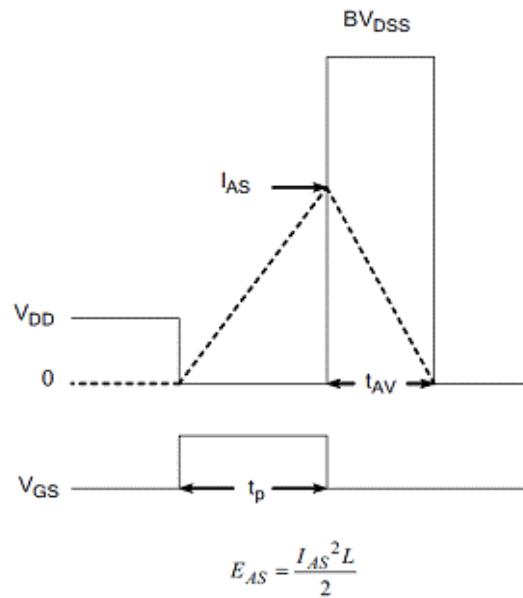
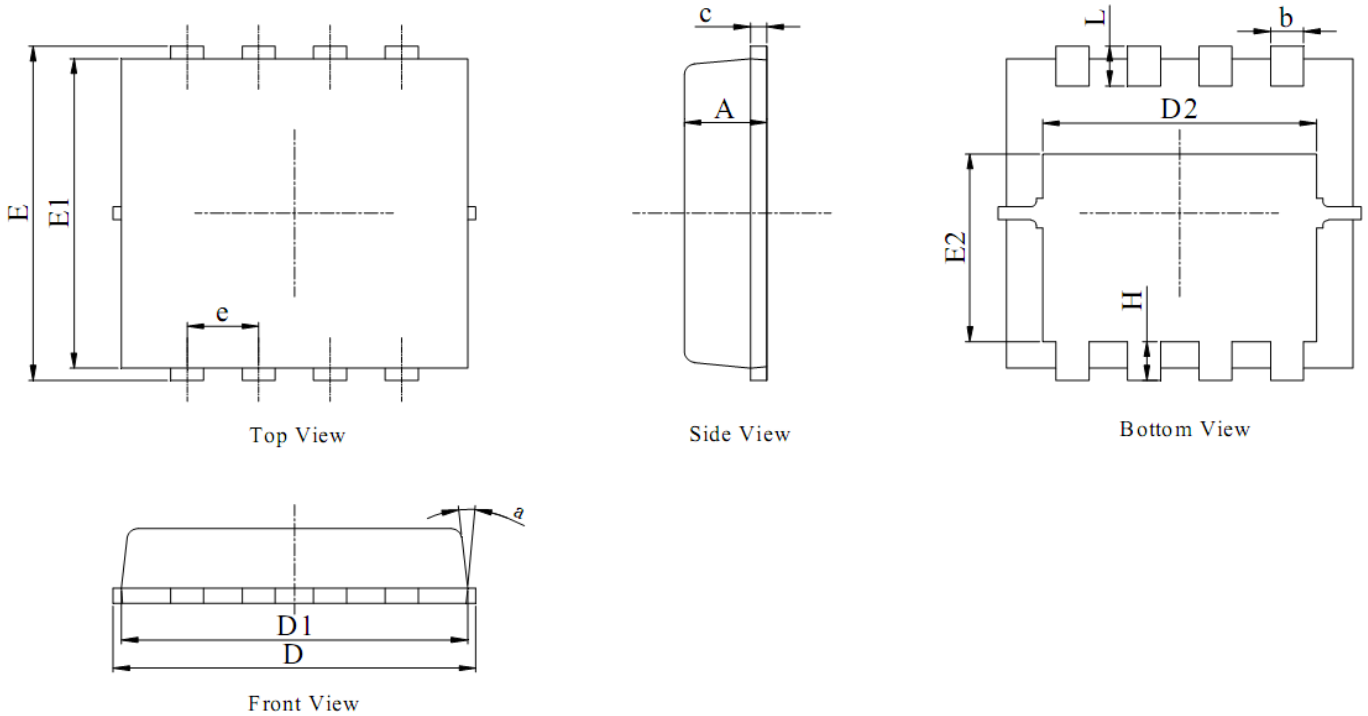
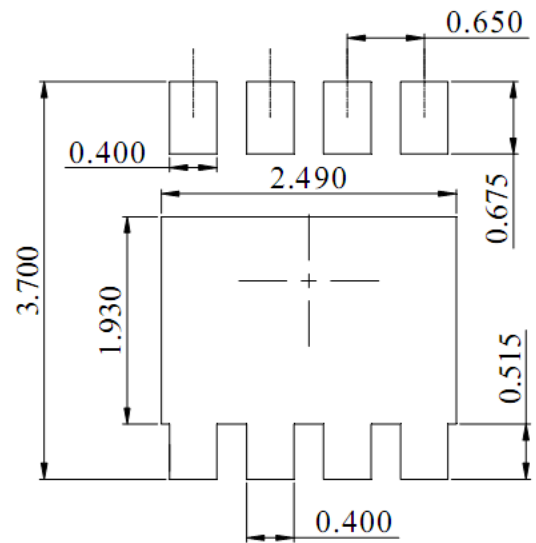


Figure 24. Unclamped Inductive Switching Waveforms

Package Mechanical Data-PDFN3333-8L-Single

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS: MILLIMETERS